

UNISONIC TECHNOLOGIES CO., LTD

15N25 Preliminary Power MOSFET

15A, 250V N-CHANNEL POWER MOSFET

■ DESCRIPTION

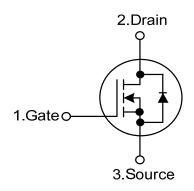
The UTC **15N25** is an N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{\text{DS(ON)}}$, high switching speed, high current capacity and low gate charge.

The UTC **15N25** is universally applied in low voltage such as automotive, high efficiency switching for DC/DC converters and DC motor control, etc.

■ FEATURES

- * $R_{DS(ON)}$ <0.32 Ω @ V_{GS} =10V, I_D =7.5A
- * Low Gate Charge (Typical 20nC)
- * Low C_{RSS} (Typical 25pF)
- * High Switching Speed

■ SYMBOL

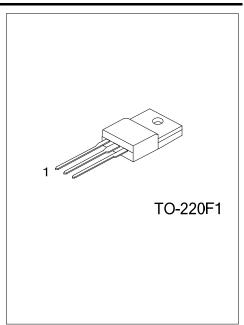


ORDERING INFORMATION

Ordering Number		Dooksas	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
15N25L-TF1-T	15N25G-TF1-T	TO-220F1	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source

15N25L-TF1-T (1)Packing Type (2)Package Type (2)Package Type (3)Lead Free (3) L: Lead Free, G: Halogen Free



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■ ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	250	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I _D	15	Α
	Pulsed	I_{DM}	60	Α
Single Pulsed Avalanche Current		I _{AS}	15	Α
Single Pulsed Avalanche Energy		E _{AS}	340	mJ
Power Dissipation		P_{D}	83	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	110	°C/W	
Junction to Case	θ _{JC}	1.5	°C/W	

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS MIN		TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V				V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =250V, V _{GS} =0V			1	μΑ		
Gate-Source Leakage Current		V_{GS} =+30V, V_{DS} =0V			+100	nΑ		
Reverse	I_{GSS}	V_{GS} =-30V, V_{DS} =0V			-100	nΑ		
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$			4	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =7.5A		0.29	0.32	Ω		
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		830	1080	pF		
Output Capacitance	Coss			200	260	pF		
Reverse Transfer Capacitance	C _{RSS}			25	33	pF		
SWITCHING PARAMETERS								
Total Gate Charge	Q_{G}			67	75	nC		
Gate to Source Charge	Q_{GS}	V_{GS} =10V, V_{DD} =50V, I_{D} =1.3A		15		nC		
Gate to Drain Charge	Q_{GD}			18		nC		
Turn-ON Delay Time	t _{D(ON)}			40	50	ns		
Rise Time	t _R	V_{DD} =30V, I_{D} =0.5A, R_{G} =25 Ω ,		50	60	ns		
Turn-OFF Delay Time	t _{D(OFF)}	V _{GS} =10V, R _L =30 Ω		130	140	ns		
Fall-Time	t _F			50	65	ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous	I.				15	Α		
Current	Is				10	^		
Maximum Body-Diode Pulsed Current	I _{SM}				60	Α		
Drain-Source Diode Forward Voltage	V_{SD}	I _S =15A, V _{GS} =0V			1.5	V		

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